Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD package: 1.0 x 0.6 x 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-410	mA
Static charact	eristics						,
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 25 °C		-	1.2	1.4	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZ1200UPE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ1200UPE	ZL

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-410	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-260	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-1.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain d	liode		1		'	
Is	source current	T _{amb} = 25 °C	[1]	-	-410	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

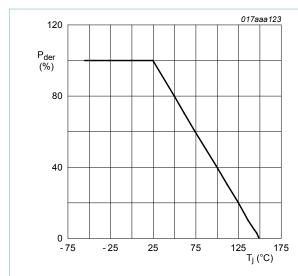


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

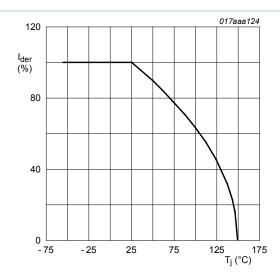


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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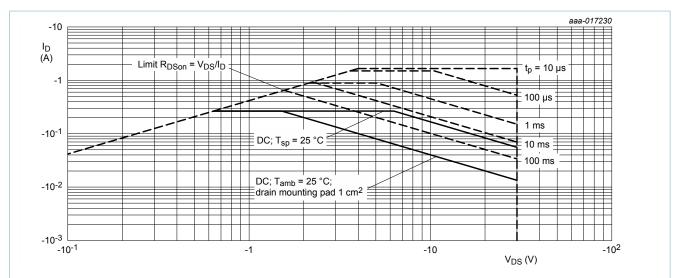


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uily a)	thermal resistance		[1]	-	350	405	K/W
	from junction to ambient		[2]	-	270	310	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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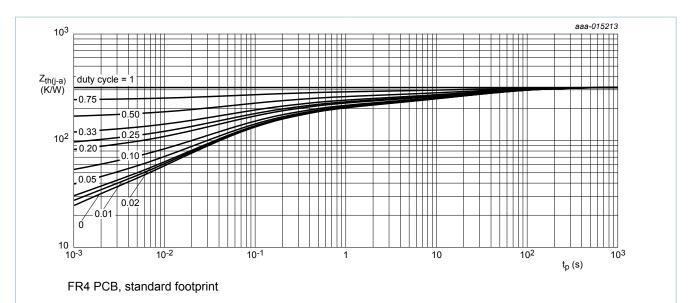
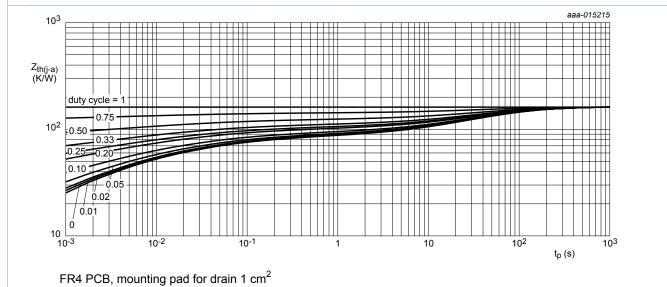


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
I _{GSS} gate leakage current	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source resistance	drain-source on-state	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 25 °C	-	1.2	1.4	Ω
	resistance	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 150 °C	-	2	2.4	Ω
		V_{GS} = -2.5 V; I_D = -320 mA; T_j = 25 °C	-	1.7	2.3	Ω
		V_{GS} = -1.8 V; I_D = -80 mA; T_j = 25 °C	-	2.1	3.1	Ω
		V _{GS} = -1.5 V; I _D = -10 mA; T _j = 25 °C	-	3	5.1	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -410 mA; T_j = 25 °C	-	820	-	mS
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = -15 V; I _D = -410 mA;	-	0.7	1.2	nC
Q_{GS}	gate-source charge	V _{GS} = -4.5 V; T _j = 25 °C	-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	43.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.9	-	pF
C _{rss}	reverse transfer capacitance		-	4.2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -15 V; I _D = -410 mA;	-	3	-	ns
t _r	rise time	$V_{GS} = -4.5 \text{ V}; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	14	-	ns
t _f	fall time		-	5	-	ns
Source-dra	in diode		I	1	1	
V _{SD}	source-drain voltage	I_S = -410 mA; V_{GS} = 0 V; T_j = 25 °C	-	-0.95	-1.2	V
			1	1	1	1

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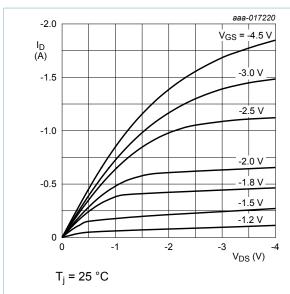
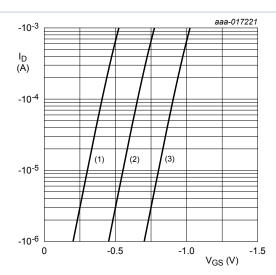


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $V_{DS} = -5 V$

T_j = 25 °C

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

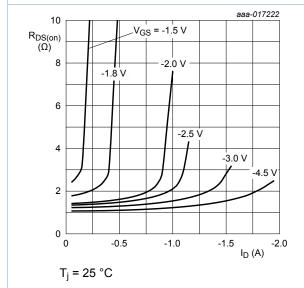


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

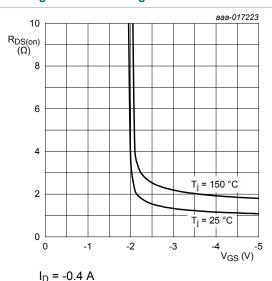


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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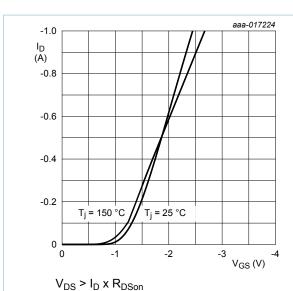


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

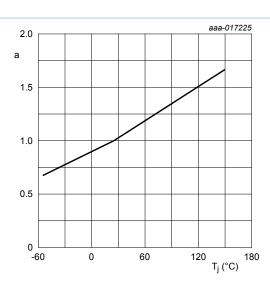
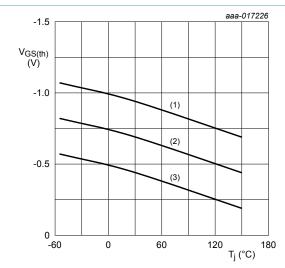


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

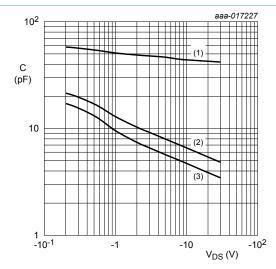
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = -250 \mu A; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

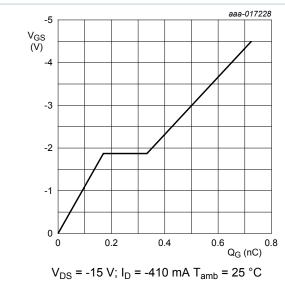


 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{DS}

V_{GS(pl)}

V_{GS(th)}

Q_{GS1} Q_{GS2}

Q_{GS} Q_{G(tot)}

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Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

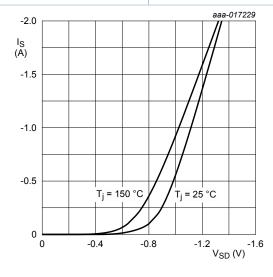
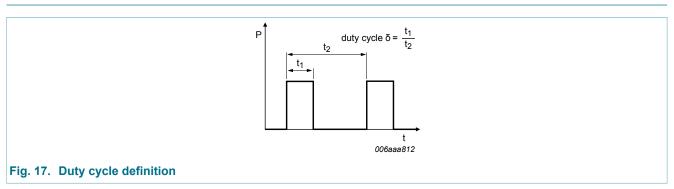


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

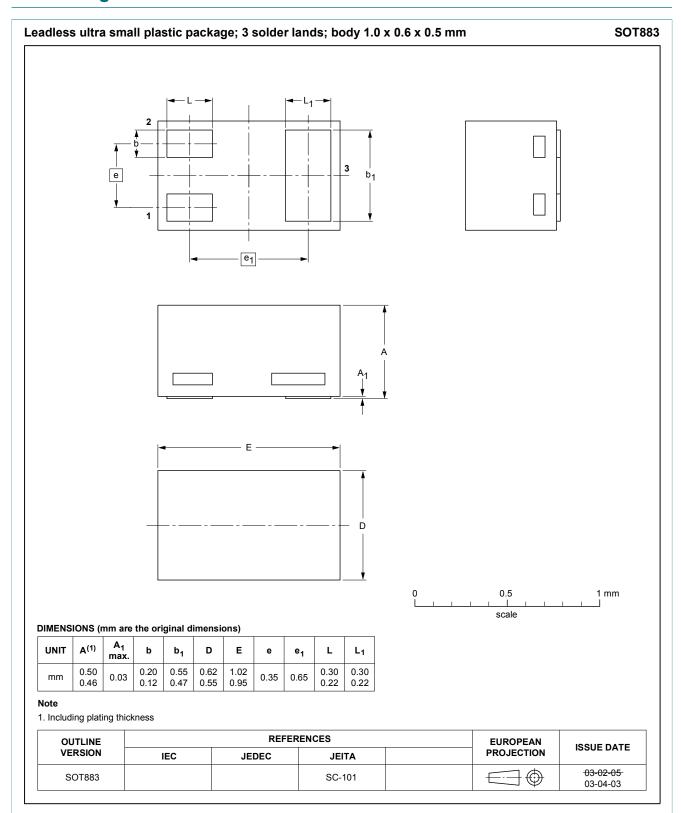
 $V_{GS} = 0 V$



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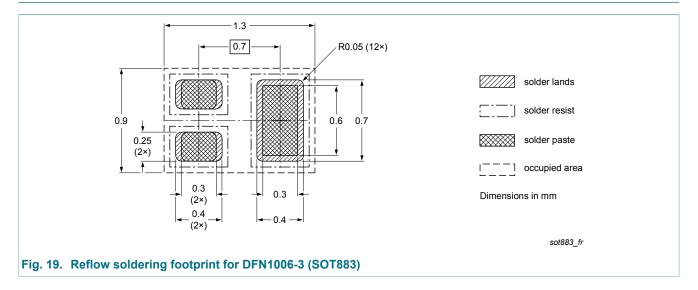
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ1200UPE v.1	20150325	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

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Product [short] data sheet	Production	This document contains the product specification.

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